SKKT 132 H4, SKKH 132 H4

THYRISTOR BRIDGE,SCR BRIDGE

SEMIPACK® 2

Thyristor / Diode Modules

SKKH 132 H4

SKKT 132 H4

Features

- Heat transfer through aluminium oxide ceramic isolated metal baseplate
- Hard soldered joints for high reliability
- UL recognized, file no. E 63 532

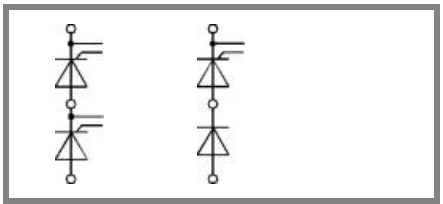
Typical Applications

- DC motor control (e. g. for machine tools)
- Temperature control (e. g. for ovens, chemical processes)
- Professional light dimming (studios, theaters)

1) See the assembly instructions

V_{RSM} V	V_{RRM}, V_{DRM} V	I_{TRMS} = 220 A (maximum value for continuous operation) I_{TAV} = 132 A (sin. 180; T_c = 84 °C)		
2100	2000	SKKT 132/20E H4	SKKH 132/20E H4	
2300	2200	SKKT 132/22E H4	SKKH 132/22E H4	

Symbol	Conditions	Values	Units
I_{TAV}	sin. 180; T_c = 85 (100) °C;	128 (90)	A
I_{TSM}	T_{vj} = 25 °C; 10 ms	4500	A
	T_{vj} = 125 °C; 10 ms	3800	A
i²t	T_{vj} = 25 °C; 8,3 ... 10 ms	100000	A²s
	T_{vj} = 125 °C; 8,3 ... 10 ms	72000	A²s
V_T	T_{vj} = 25 °C; I_T = 500 A	max. 1,8	V
$V_{T(TO)}$	T_{vj} = 125 °C	max. 1,1	V
r_T	T_{vj} = 125 °C	max. 2	mΩ
I_{DD}; I_{RD}	T_{vj} = 125 °C; V_{RD} = V_{RRM}; V_{DD} = V_{DRM}	max. 40	mA
t_{gd}	T_{vj} = 25 °C; I_G = 1 A; di_G/dt = 1 A/µs	1	µs
t_{gr}	V_D = 0,67 * V_{DRM}	2	µs
$(di/dt)_{cr}$	T_{vj} = 125 °C	max. 200	A/µs
$(dv/dt)_{cr}$	T_{vj} = 125 °C	max. 1000	V/µs
t_q	T_{vj} = 125 °C	50 ... 150	µs
I_H	T_{vj} = 25 °C; typ. / max.	150 / 400	mA
I_L	T_{vj} = 25 °C; R_G = 33 Ω; typ. / max.	300 / 1000	mA
V_{GT}	T_{vj} = 25 °C; d.c.	min. 2	V
I_{GT}	T_{vj} = 25 °C; d.c.	min. 150	mA
V_{GD}	T_{vj} = 125 °C; d.c.	max. 0,25	V
I_{GD}	T_{vj} = 125 °C; d.c.	max. 10	mA
$R_{th(j-c)}$	cont.; per thyristor / per module	0,17 / 0,085	K/W
$R_{th(j-c)}$	sin. 180; per thyristor / per module	0,18 / 0,09	K/W
$R_{th(j-c)}$	rec. 120; per thyristor / per module	0,2 / 0,1	K/W
$R_{th(c-s)}$	per thyristor / per module	0,1 / 0,05	K/W
T_{vj}		- 40 ... + 125	°C
T_{stg}		- 40 ... + 125	°C
V_{isol}	a. c. 50 Hz; r.m.s.; 1 s / 1 min.	4800 / 4000	V~
M_s	to terminal	5 ± 15 %[1)]	Nm
M_t	to terminal	5 ± 15 %	Nm
a		5 * 9,81	m/s²
m	approx.	175	g
Case	SKKT	A 21	
	SKKH	A 22	



SKKT SKKH

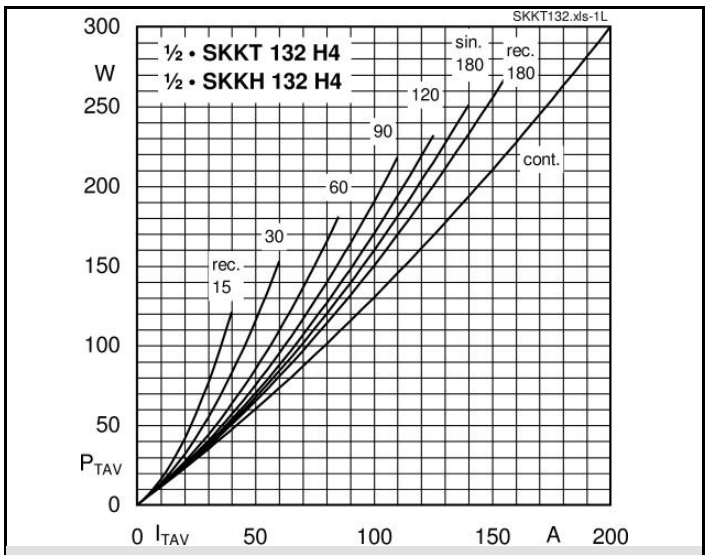


Fig. 1L Power dissipation per thyristor vs. on-state current

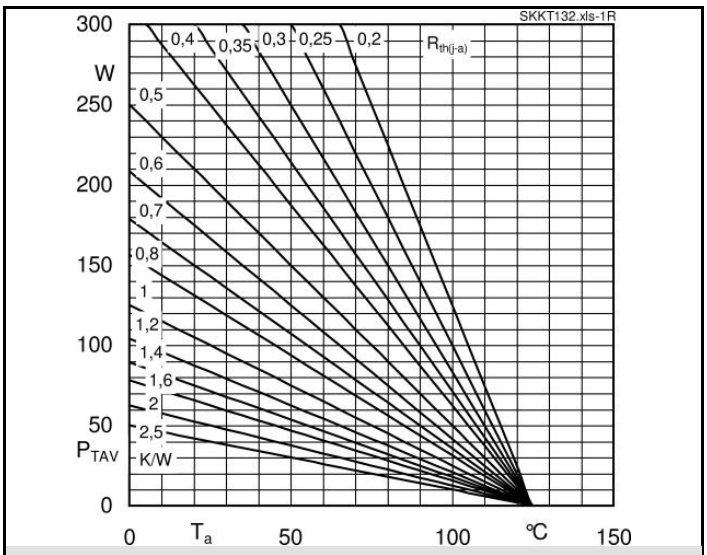


Fig. 1R Power dissipation per thyristor vs. ambient temp.

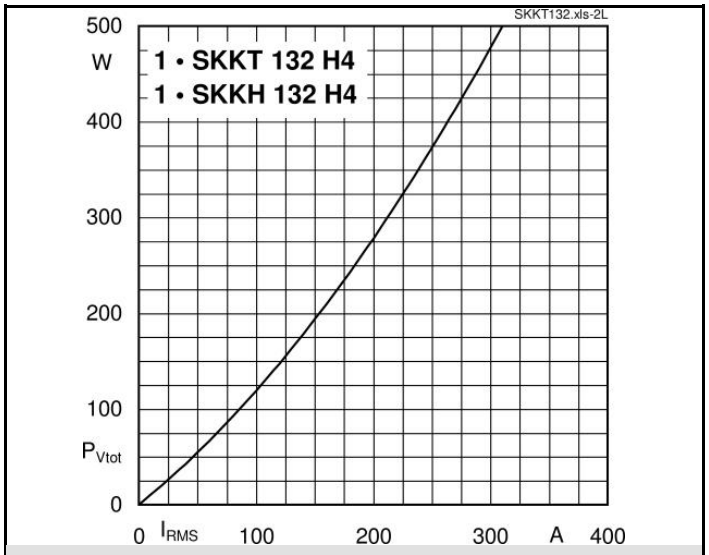


Fig. 2L Power dissipation per module vs. rms current

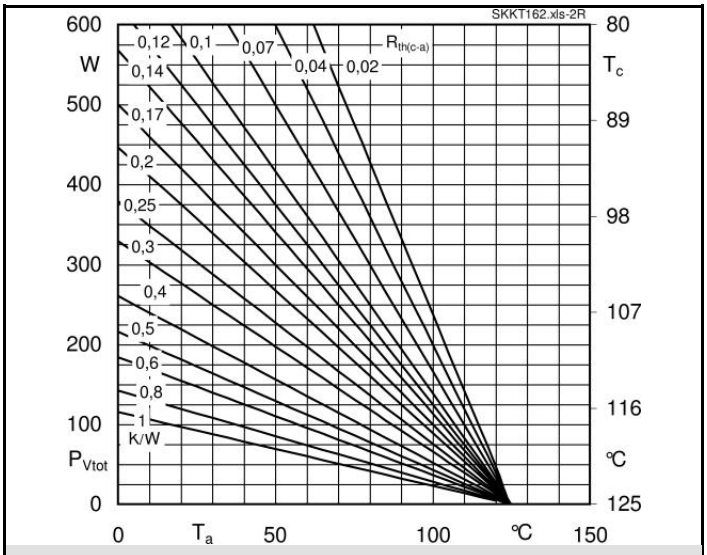


Fig. 2R Power dissipation per module vs. case temp.

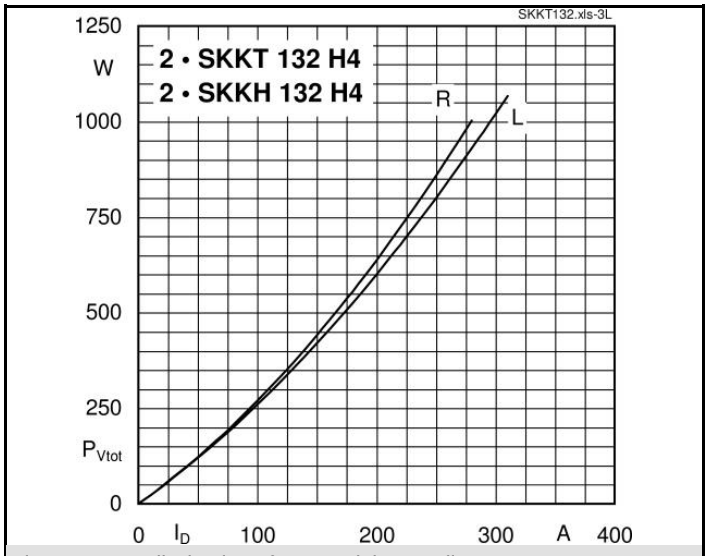


Fig. 3L Power dissipation of two modules vs. direct current

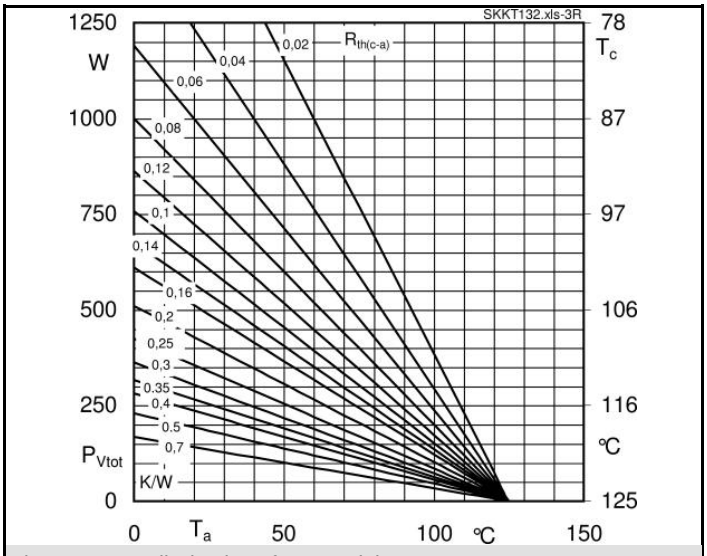


Fig. 3R Power dissipation of two modules vs. case temp.

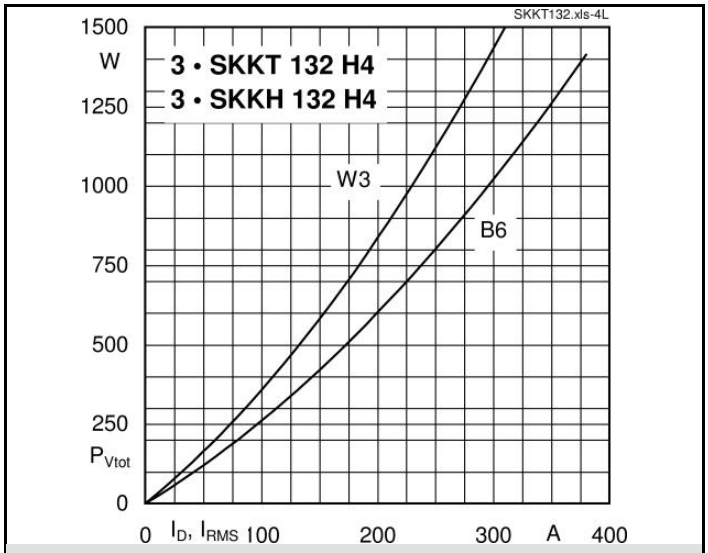


Fig. 4L Power dissipation of three modules vs. direct and rms current

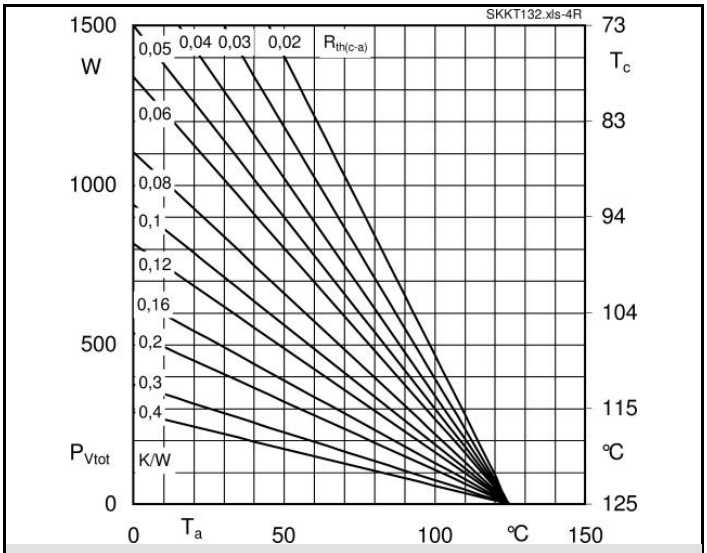


Fig. 4R Power dissipation of three modules vs. case temp.

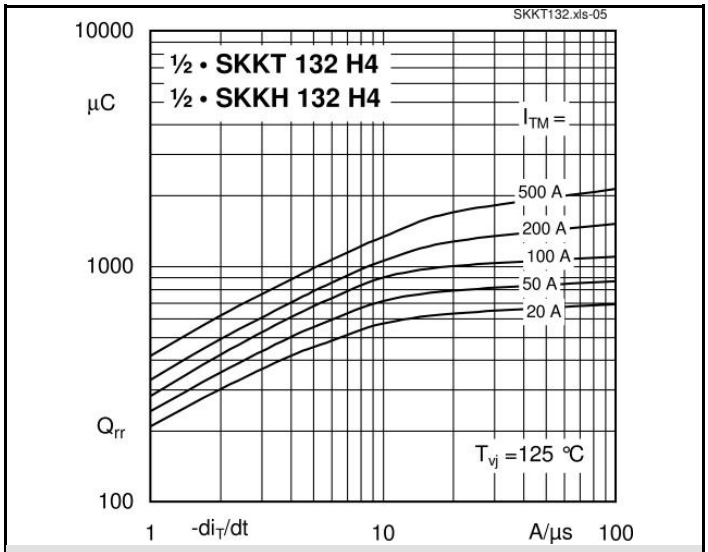


Fig. 5 Recovered charge vs. current decrease

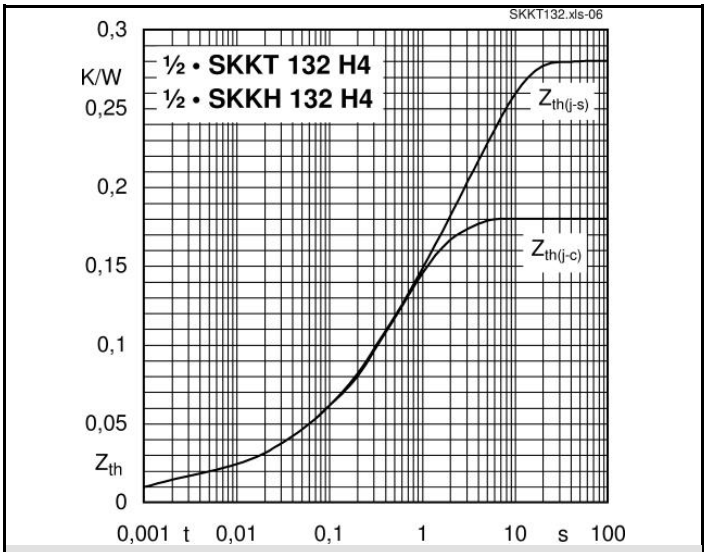


Fig. 6 Transient thermal impedance vs. time

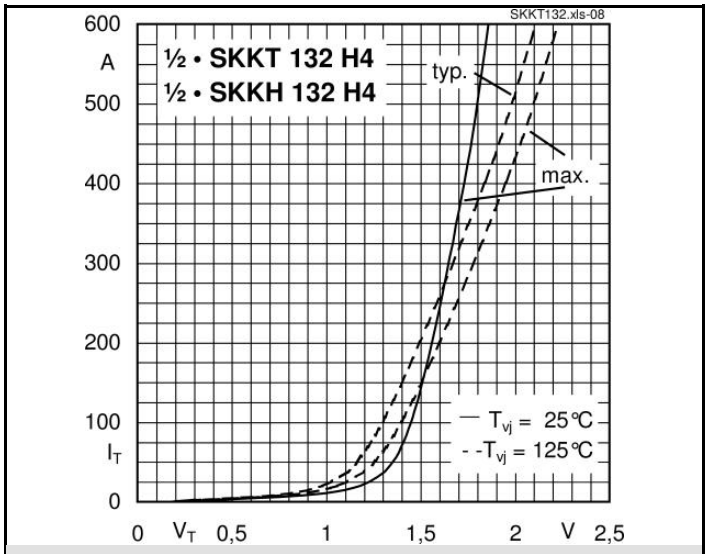


Fig. 7 On-state characteristics

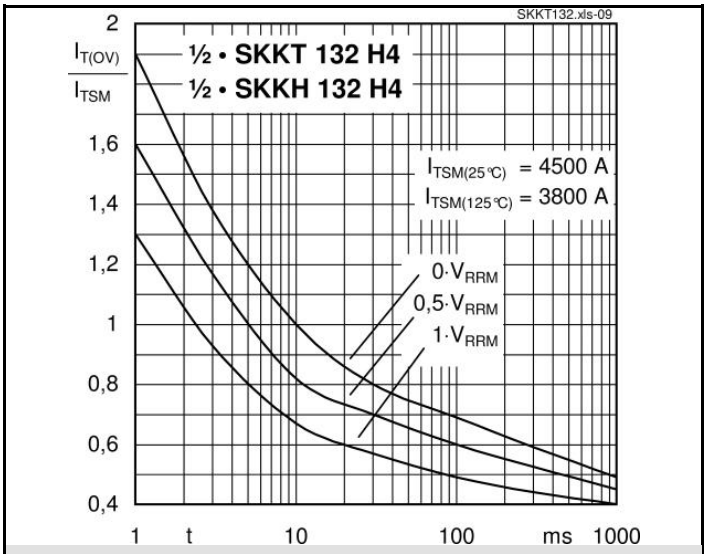


Fig. 8 Surge overload current vs. time

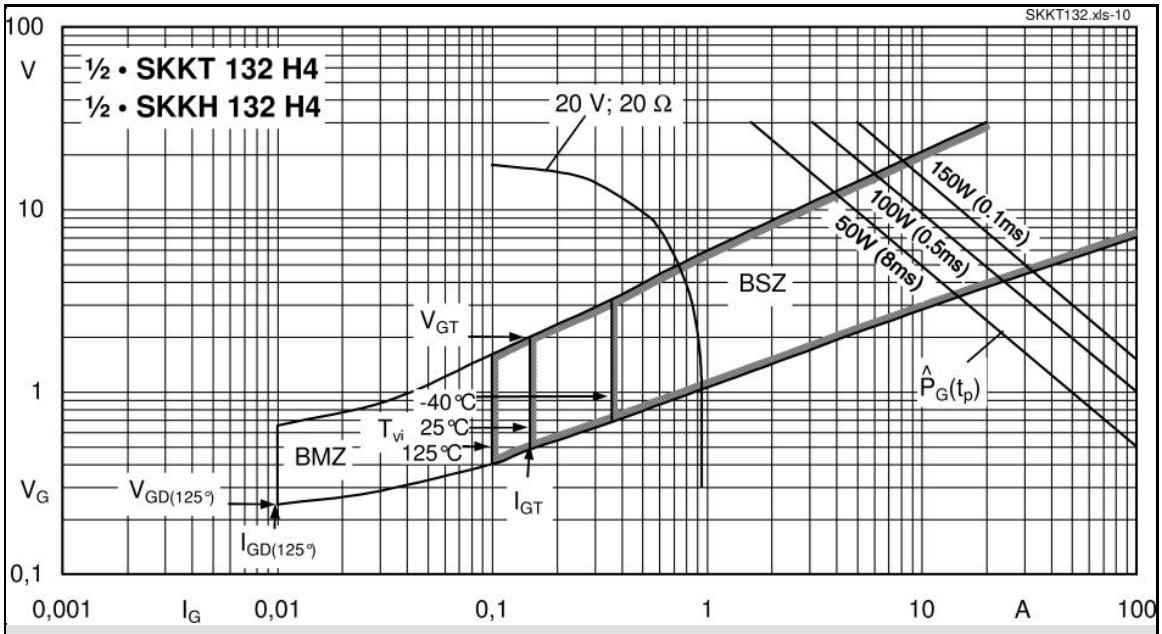
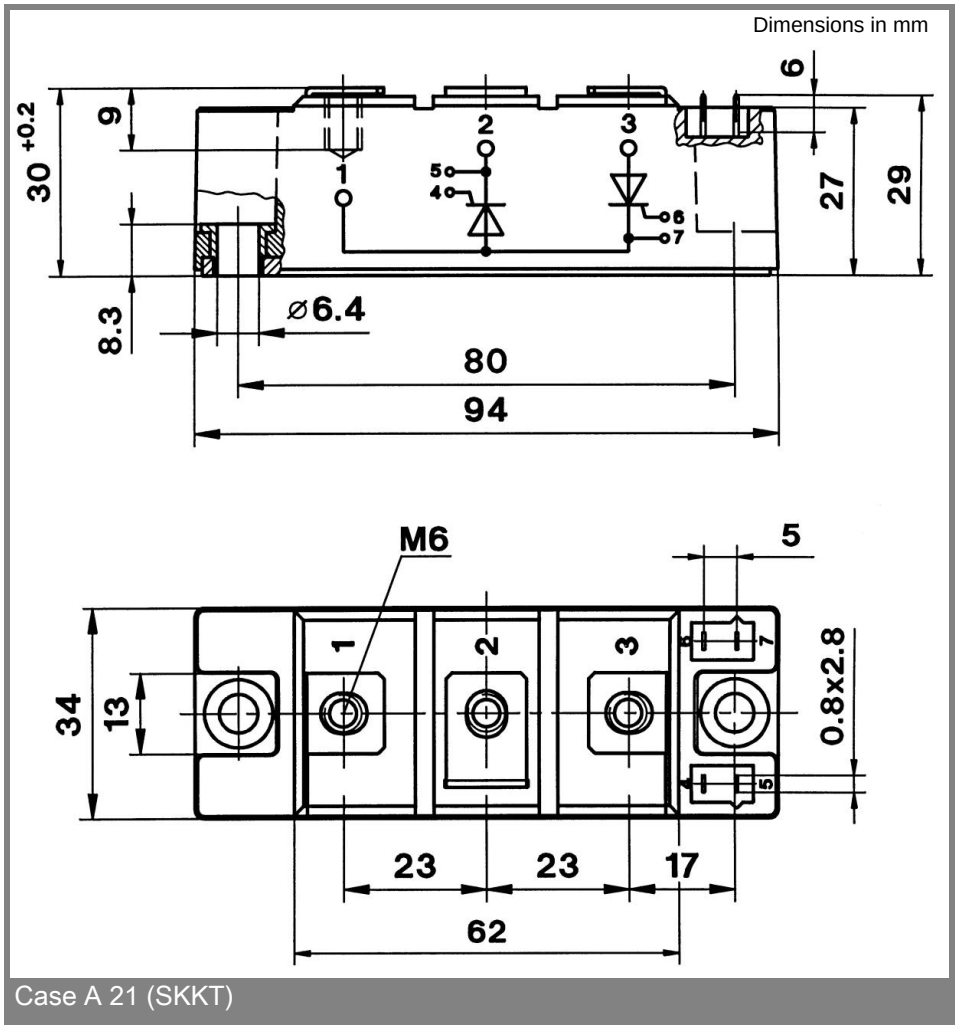
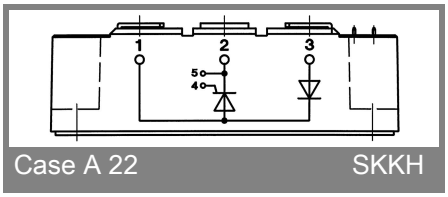


Fig. 9 Gate trigger characteristics



Case A 21 (SKKT)



Case A 22 SKKH

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